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#### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C	
40V	$10m\Omega$ @ $V_{GS} = 10V$	50A	

### **Features and Benefits**

- Rated to +175°C ideal for high ambient temperature environments
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

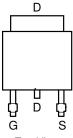
- DC-DC Converters
- Power Management Functions
- Analog Switch

### **Mechanical Data**

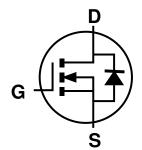
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View



Top View Pin Out



Internal Schematic

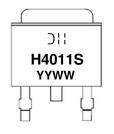
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMNH4011SK3-13	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



=Manufacturer's Marking
H4011S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 14 = 2014)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			$V_{DSS}$	40	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ΙD	50 27	А
Maximum Body Diode Forward Current (Note 6)			I <sub>S</sub>	120	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	120	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	50	W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	3	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

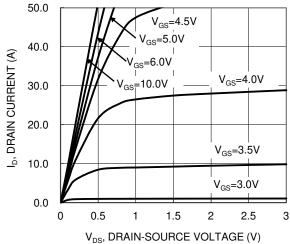
# **Electrical Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

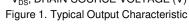
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 40V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	10	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	$V_{SD}$	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	1,405	_			
Output Capacitance	Coss	_	247	_	pF	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$	
Reverse Transfer Capacitance	Crss	_	108	_			
Gate Resistance	$R_{G}$		2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_g$	_	25.5	_			
Gate-Source Charge	$Q_{gs}$	_	4.6	_	nC	$V_{DS} = 20V, V_{GS} = 10V, I_{D} = 50A$	
Gate-Drain Charge	$Q_{gd}$	_	6.9	_			
Turn-On Delay Time	t <sub>D(ON)</sub>		4.6	_			
Turn-On Rise Time	t <sub>R</sub>		3.7	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3.5\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16	_	115		
Turn-Off Fall Time	t <sub>F</sub>	_	5.1	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	22.1	_	ns	I <sub>F</sub> = 50A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		13.4	_	nC	71F = 50A, αι/αι = 100A/μS	

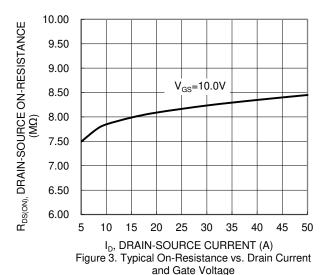
Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.









R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE 0.02  $V_{GS}=10V$ 0.018 75°C 150°C 0.016 0.014 85°C 0.012 0.01 25°C 0.008 0.006 55°C 0.004 0.002

15 20

10

I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature

25 30 35

40 45

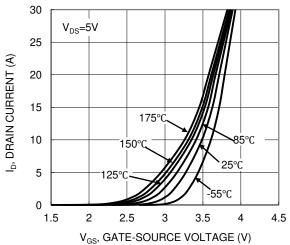


Figure 2. Typical Transfer Characteristic

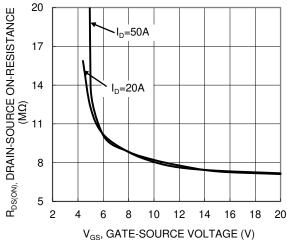
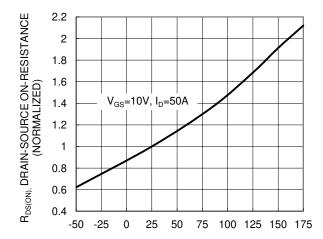


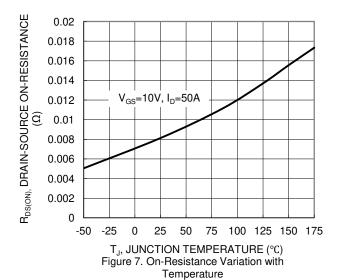
Figure 4. Typical Transfer Characteristic

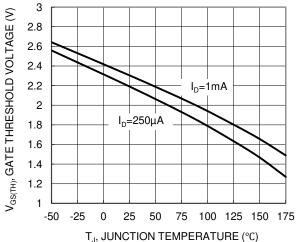


T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Temperature

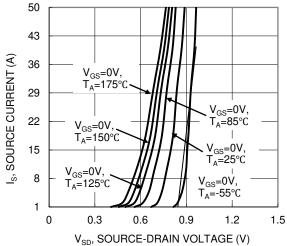
0 0 5



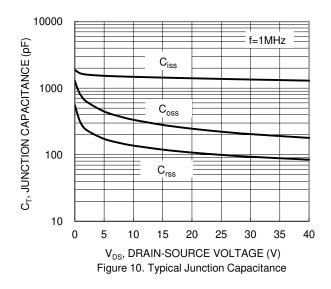


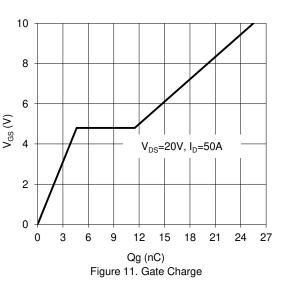


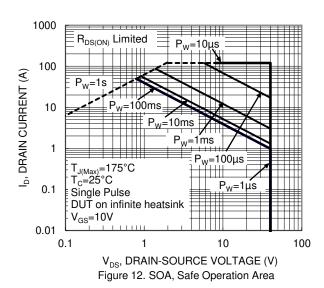
T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current









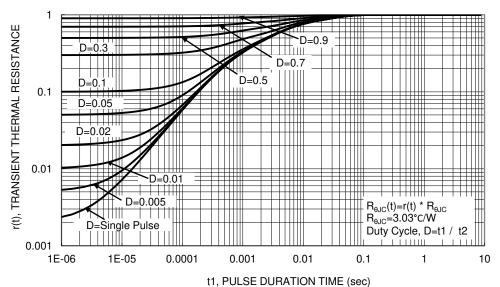
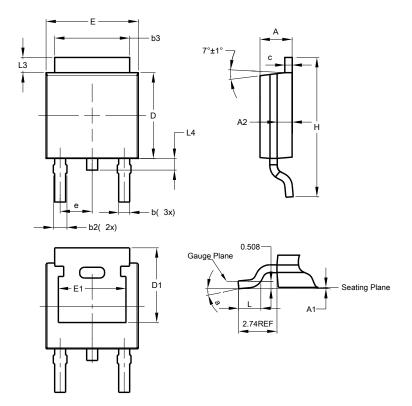


Figure 13. Transient Thermal Resistance

# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

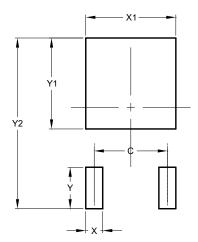


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
<b>A2</b>	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					



## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	4.572
X	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700

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